

KS54HCTLS 841/842 KS74HCTLS

10-Bit Bus Interface D-Type Latches with 3-State Outputs

T-46-07-05

Preliminary Specifications

FEATURES

- Bus-Structured Pinout
- Provides Extra Bus Driving Latches
- Necessary for Wider Address/Data Paths or Buses with Parity
- Power-Up High-Impedance State
- Function, pin-out, speed and drive compatibility with 54/74LS logic family
- Low power consumption characteristic of CMOS
- 3-State outputs with high drive current ($I_{OL} = 24 \text{ mA @ } V_{OL} = 0.5V$) for direct bus interface
- Inputs and outputs interface directly with TTL, NMOS and CMOS devices
- Wide operating voltage range: 4.5V to 5.5V
- Characterized for operation over industrial and military temperature ranges:
KS54HCTLS: -40°C to $+85^{\circ}\text{C}$
KS74HCTLS: -55°C to $+125^{\circ}\text{C}$
- Package options include plastic "small outline" packages, standard plastic and ceramic 300-mil DIPs

DESCRIPTION

These 10-bit bus interface latches feature three state outputs designed specifically for driving highly capacitive or relatively low-impedance loads. They are suitable for implementing wider buffer registers. I/O ports, bidirectional bus drivers, and working registers.

The ten latches are transparent D-type. The '841 has noninverting data (D) inputs and the '842 has inverting (\bar{D}) inputs.

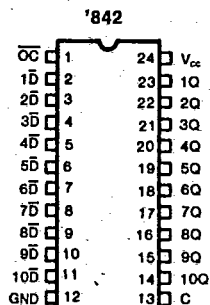
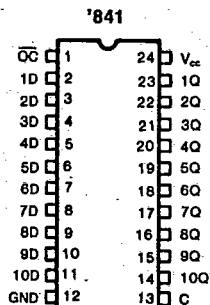
A buffered output control (\overline{OC}) input can be used to place the ten outputs in either a normal logic state (high or low levels) or a high-impedance state. The high-impedance state and increased drive provide the capability to drive the bus lines in a bus-organized system without need for interface or pull-up components.

The output control does not affect the internal operation of the latches. Old data can be retained or new data can be entered while the outputs are off.

These devices provide speeds and drive capability equivalent to their LSTTL counterparts and yet maintain CMOS power levels. The input and output voltage levels allow direct interface with TTL, NMOS and CMOS devices without any external components.

All inputs and outputs are protected from damage due to static discharge by internal diode clamps to V_{CC} and ground.

PIN CONFIGURATIONS



FUNCTION TABLES

'841

INPUTS			OUTPUT
\overline{OC}	C	D	Q
L	H	H	H
L	H	L	L
L	L	X	Q_0
H	X	X	Z

'842

INPUTS			OUTPUT
\overline{OC}	C	\bar{D}	Q
L	H	H	L
L	H	L	H
L	L	X	Q_0
H	X	X	Z

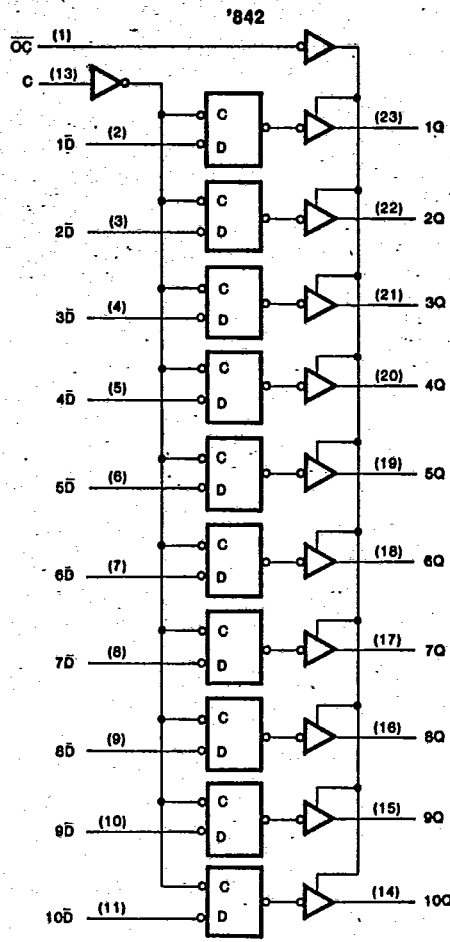
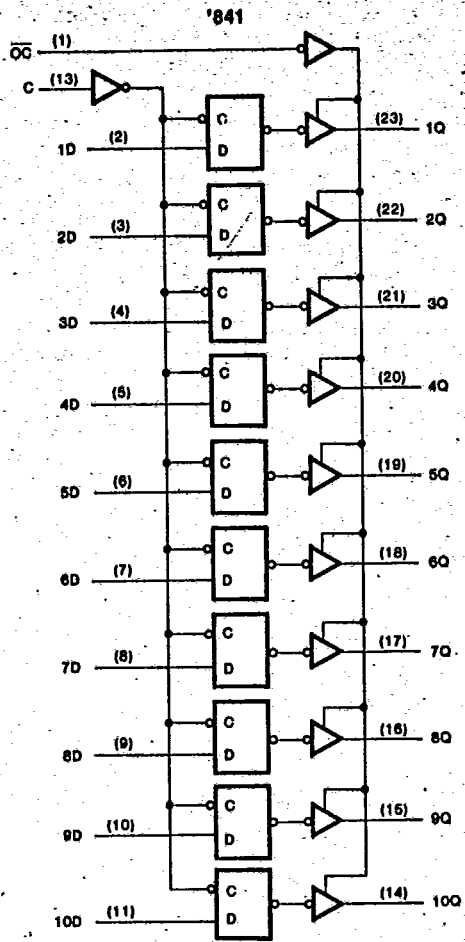
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KS54HCTL5 841/842
KS74HCTL5

10-Bit Bus Interface D-Type Latches with 3-State Outputs

T-46-07-05

LOGIC DIAGRAMS



KS54HCTLS 841/842
KS74HCTLS

10-Bit Bus Interface D-Type
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Absolute Maximum Ratings*

Supply Voltage Range V_{CC} -0.5V to +7V
 DC Input Diode Current, I_{IK}
 ($V_I < -0.5V$ or $V_I > V_{CC} + 0.5V$) ± 20 mA
 DC Output Diode Current, I_{OK}
 ($V_O < -0.5V$ or $V_O > V_{CC} + 0.5V$) ± 20 mA
 Continuous Output Current Per Pin, I_O
 ($-0.5V < V_O < V_{CC} + 0.5V$) ± 70 mA
 Continuous Current Through
 V_{CC} or GND pins ± 250 mA
 Storage Temperature Range, T_{stg} -65°C to +150°C
 Power Dissipation Per Package, P_D [†] 500 mW

* Absolute Maximum Ratings are those values beyond which permanent damage to the device may occur. These are stress ratings only and functional operation of the device at or beyond them is not implied. Long exposure to these conditions may affect device reliability.

† Power Dissipation temperature derating:
 Plastic Package (N): -12mW/°C from 65°C to 85°C
 Ceramic Package (J): -12mW/°C from 100°C to 125°C

Recommended Operating Conditions

Supply Voltage, V_{CC} 4.5V to 5.5V
 DC Input & Output Voltages*, V_{IN} , V_{OUT} 0V to V_{CC}
 Operating Temperature
 Range KS74HCTLS: -40°C to +85°C
 KS54HCTLS: -55°C to +125°C
 Input Rise & Fall Times, t_r , t_f Max 500 ns

* Unused inputs must always be tied to an appropriate logic voltage level (either V_{CC} or GND)

DC ELECTRICAL CHARACTERISTICS ($V_{CC}=5V \pm 10\%$ Unless Otherwise Specified)

Characteristic	Symbol	Test Conditions	$T_a = 25^\circ C$			Unit	
			Typ	KS74HCTLS $T_a = -40^\circ C$ to $+85^\circ C$	KS54HCTLS $T_a = -55^\circ C$ to $+125^\circ C$		
Minimum High-Level Input Voltage	V_{IH}			2.0	2.0	2.0	V
Maximum Low-Level Input Voltage	V_{IL}			0.8	0.8	0.8	V
Minimum High-Level Output Voltage	V_{OH}	$V_{IN}=V_{IH}$ or V_{IL} $I_O = -20\mu A$ $I_O = -6mA$	V_{CC} 4.2	$V_{CC} - 0.1$ 3.98	$V_{CC} - 0.1$ 3.84	$V_{CC} - 0.1$ 3.7	V
Maximum Low-Level Output Voltage	V_{OL}	$V_{IN}=V_{IH}$ or V_{IL} $I_O = 20\mu A$ $I_O = 12mA$ $I_O = 24mA$	0	0.1 0.26 0.39	0.1 0.33 0.5	0.1 0.4	V
Maximum Input Current	I_{IN}	$V_{IN}=V_{CC}$ or GND		± 0.1	± 1.0	± 1.0	μA
Maximum 3-State Leakage Current	I_{OZ}	Output Enable = V_{IH} $V_{OUT}=V_{CC}$ or GND		± 0.5	± 5.0	± 10.0	μA
Maximum Quiescent Supply Current	I_{CC}	$V_{IN}=V_{CC}$ or GND $I_{OUT}=0\mu A$		8.0	80.0	160.0	μA
Additional Worst Case Supply Current	ΔI_{CC}	per input pin $V_I=2.4V$ other inputs: at V_{CC} or GND $I_{OUT}=0\mu A$		2.7	2.9	3.0	mA

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KS54HCTLS
KS74HCTLS **841/842****10-Bit Bus Interface D-Type
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T-46-07-05

AC ELECTRICAL CHARACTERISTICS (Input t_r , $t_f \leq 6$ ns), HCTLS841, HCTLS842

Characteristic	Symbol	Conditions†	$T_a = 25^\circ\text{C}$ $V_{CC} = 5.0\text{V}$		KS74HCTLS $T_a = -40^\circ\text{C to } +85^\circ\text{C}$ $V_{CC} = 5.0\text{V} \pm 10\%$		KS54HCTLS $T_a = -55^\circ\text{C to } +125^\circ\text{C}$ $V_{CC} = 5.0\text{V} \pm 10\%$		Unit
			Typ	Guaranteed Limits					
Maximum Propagation Delay, Data to Q	t_{PLH}	$C_L = 50\text{pF}$ $C_L = 150\text{pF}$	15 18	20 23	25 30	30 36	30 36	36 42	ns
	t_{PHL}	$C_L = 50\text{pF}$ $C_L = 150\text{pF}$	15 18	20 23	25 30	30 36	30 36	36 42	
Maximum Propagation Delay, C to any Q	t_{PLH}	$C_L = 50\text{pF}$ $C_L = 150\text{pF}$	21 24	28 31	35 40	40 48	42 48	48 54	ns
	t_{PHL}	$C_L = 50\text{pF}$ $C_L = 150\text{pF}$	21 24	28 31	35 40	40 48	42 48	48 54	
Maximum Output Enable Time, \overline{OC} to any Q	t_{pZH}	$R_L = 1\text{k}\Omega$ $C_L = 50\text{pF}$ $C_L = 150\text{pF}$	18 21	24 27	30 35	35 42	36 42	42 48	ns
	t_{pZL}	$C_L = 50\text{pF}$ $C_L = 150\text{pF}$	18 21	24 27	30 35	35 42	36 42	42 48	
Maximum Output Disable Time, \overline{OC} to any Q	t_{pHZ}	$R_L = 1\text{k}\Omega$	18	24	30	36	36	42	ns
	t_{pLZ}	$C_L = 50\text{pF}$	18	24	30	36	36	42	
Minimum Pulse Width, C High	t_w		15	20	25	30	30	36	ns
Minimum Setup Time, Data before $C\downarrow$	t_{su}		12	16	20	24	24	30	ns
Minimum Hold Time, Data after $C\downarrow$	t_h		6	8	10	12	12	15	ns
Maximum Input Capacitance	C_{IN}		5						pF
Maximum Output Capacitance	C_{OUT}		10						pF
Power Dissipation Capacitance* (per stage)	C_{PD}	$\overline{OC} = V_{CC}$	5						pF
		$\overline{OC} = \text{GND}$	30						

* C_{PD} determines the no-load dynamic power dissipation: $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$.

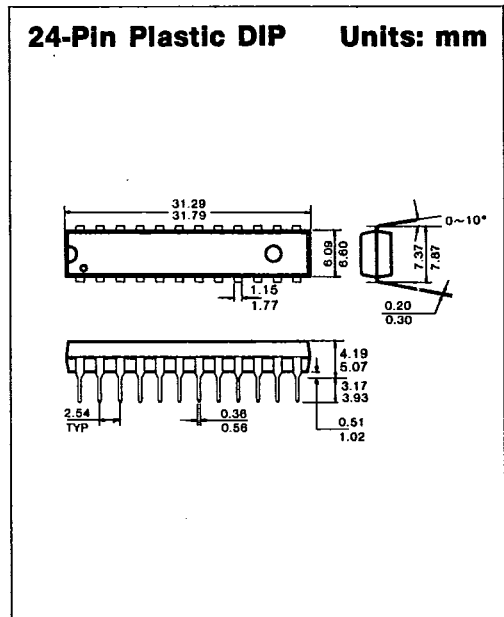
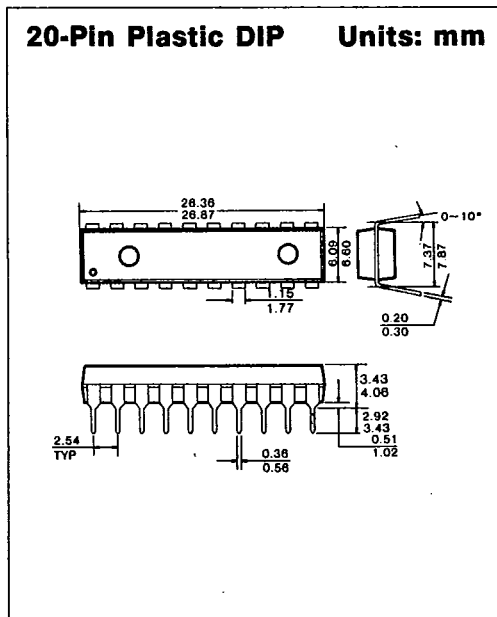
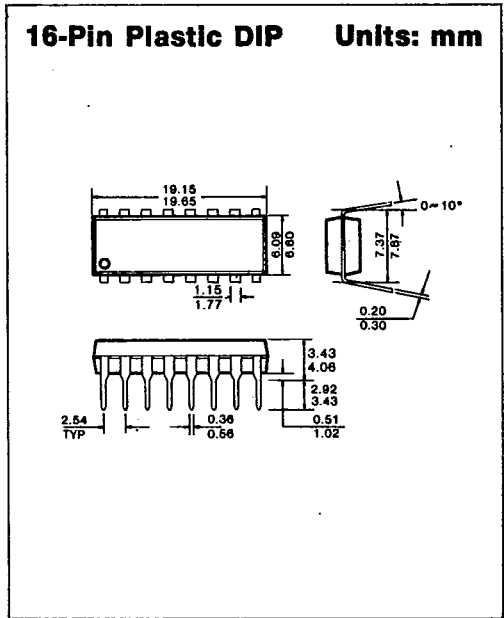
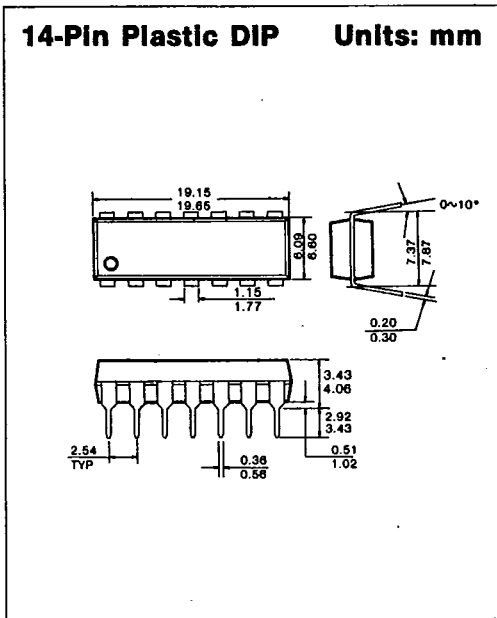
† For AC switching test circuits and timing waveforms see section 2.



PACKAGE DIMENSIONS

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1. PLASTIC PACKAGES



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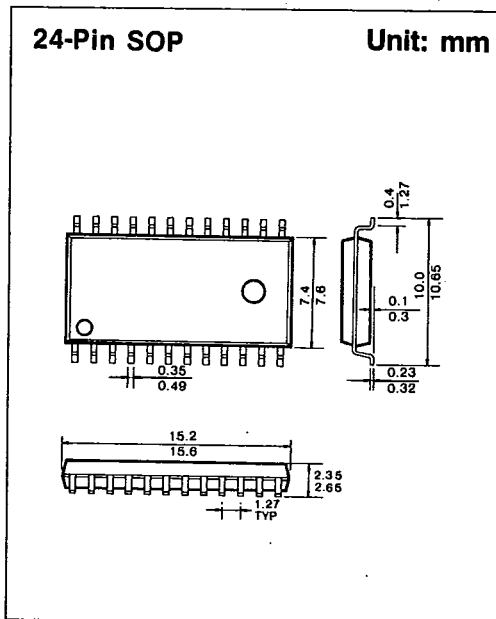
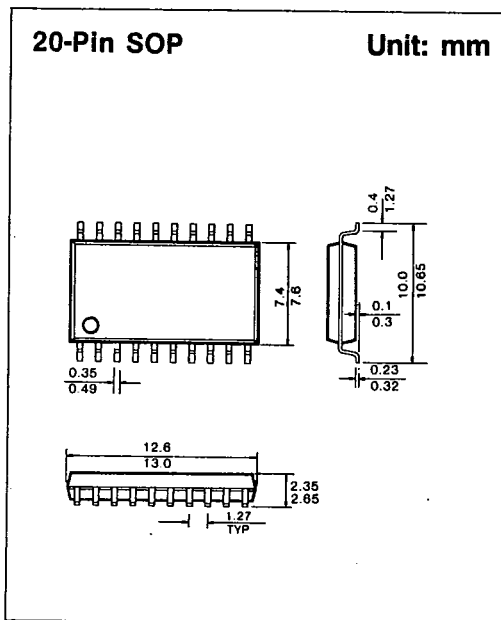
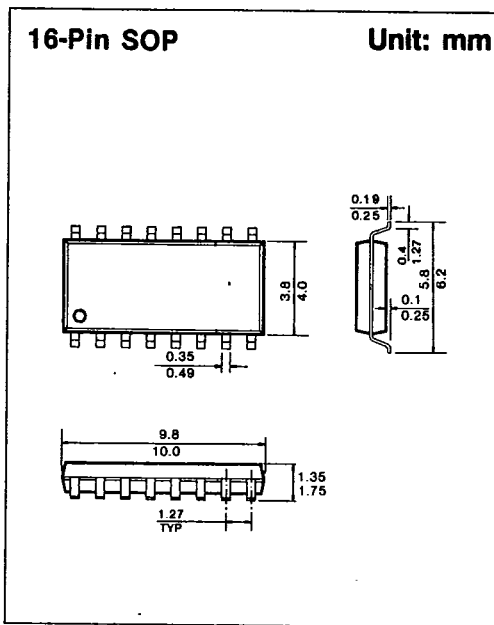
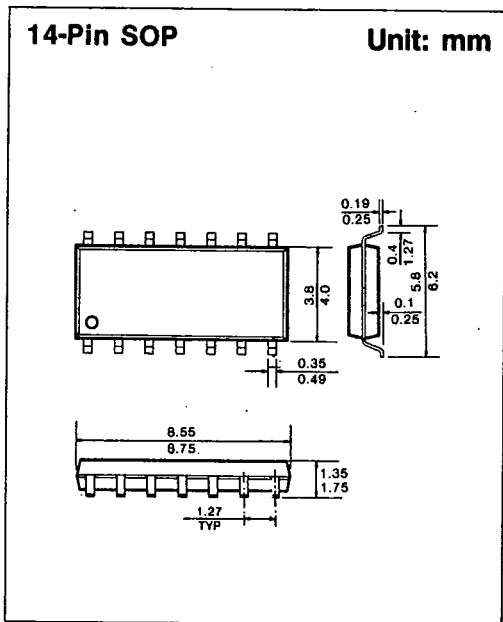
SAMSUNG SEMICONDUCTOR

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PACKAGE DIMENSIONS

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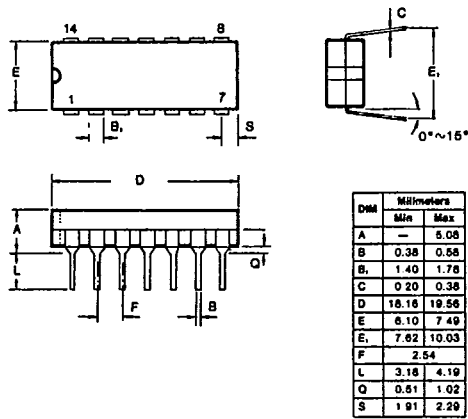


PACKAGE DIMENSIONS

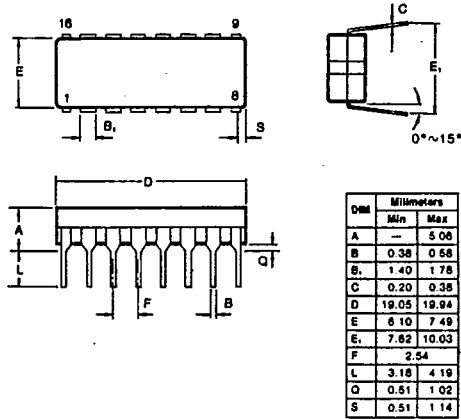
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2. CERAMIC PACKAGES

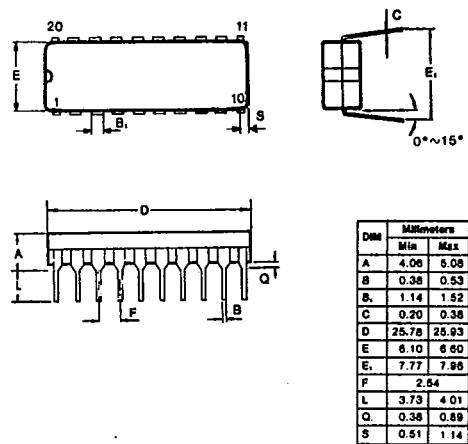
14-Pin Ceramic DIP Units: mm



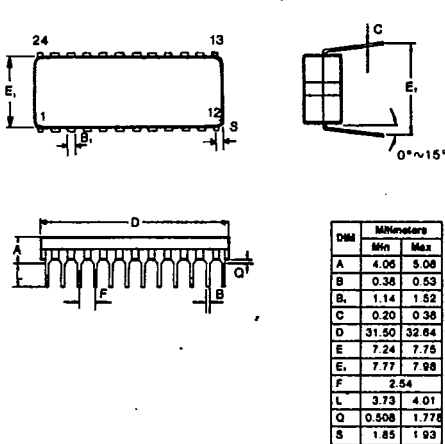
16-Pin Ceramic DIP Units: mm



20-Pin Ceramic DIP Units: mm



24-Pin Ceramic DIP Units: mm



7